

## SBP-7137633933-1212-EP

71 to 76 GHz, Power Amplifier, 39 dB Gain, +33 dBm P<sub>sat</sub>

**SBP-7137633933-1212-EP** is a E-Band, GaAs power amplifier with a typical small signal gain of 39 dB and a nominal P<sub>sat</sub> of +33 dBm across the frequency range of 71 to 76 GHz. The DC power requirement for the amplifier is +6 V<sub>DC</sub>/ 5 A. The mechanical configuration offers an in-line structure with WR-12 waveguides and UG-387/U-M anti-cocking flanges. A heat sink is included for cooling.



### Electrical Specifications:

Parameter	Minimum	Typical	Maximum
Frequency Range	71 GHz		76 GHz
Small Signal Gain		39 dB	
P <sub>1dB</sub>		+31 dBm	
P <sub>Sat</sub>		+33 dBm	
Input Return Loss		10 dB	
Output Return Loss		12 dB	
DC Voltage		+6 V <sub>DC</sub>	
DC Supply Current (Quiescent)		3.5 A	
DC Supply Current (Saturated)		5.0 A	
Fan DC Voltage		+12 V <sub>DC</sub>	
Specification Temperature		+25°C	
Operating Temperature	0°C		+50°C

### Mechanical Specifications:

Item	Specification
Input/Output Ports	WR-12 Rectangular Waveguide with UG-387/U-M Anti-Cocking Flange
Bias	Solder Pin
Case Material	Copper
Finish	Gold Plated, Black Anodize
Weight	28 oz
Size	4.33" (L) X 3.35" (W) X 3.46" (H)
Outline	BP-HE-A-H2

### ECCN

3A001.b.4

### FEATURES

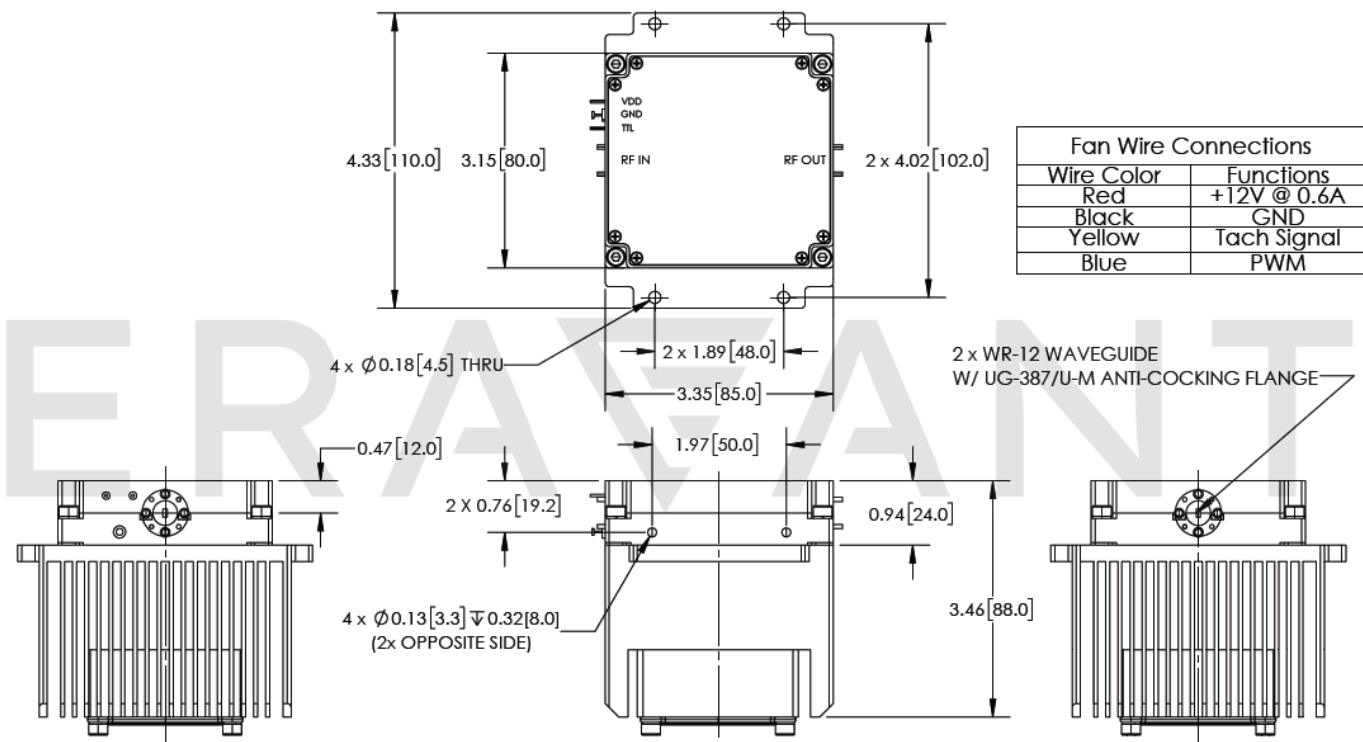
- Forced Air Cooling
- In-line Port Configuration
- High Power Output
- High Linearity

### APPLICATIONS

- Communications Systems
- Test Equipment
- Radar Systems

### SUPPLEMENTAL DETAILS

**Mechanical Outline:** Unless otherwise specified, all dimensions are in inches [millimeters])



**NOTE:**

- All data presented is collected from a sample lot. Actual data may vary unit to unit.
- Other mechanical configurations with other frequency bands are available under different model numbers.
- Eravant reserves the right to change the information presented without notice.

**CAUTION:**

- Exceeding absolute maximum ratings shown will damage the device.
- The device is static sensitive. Always follow ESD rules when working with the device.
- The case temperature of the device shall never exceed **+70°C**.
- Any foreign objects in the waveguide will cause performance degradation and possible device damage.